PSMN011-60ML

N-channel 60 V 11.3 m Ω logic level MOSFET in LFPAK33 **Product data sheet**

1. **General description**

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. **Features and benefits**

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources
- LFPAK33 package is footprint compatible with other 3.3mm types
- Qualified to 175 °C

Applications 3.

- AC-to-DC converters
- Synchronous rectification
- DC-DC converters

Quick reference data 4.

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	-	61	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	91	W
T _j	junction temperature		-55	-	175	°C
Static characte	eristics		,	'		
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	-	9.35	11.3	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12	-	11	13.1	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; V_{DS} = 30 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 14}}; \underline{\text{Fig. 15}}$	-	5.1	-	nC



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D I
2	S	source		
3	S	source		G (S)
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN011-60ML	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN011-60ML	M11L60

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	61	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	43	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	242	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	91	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode	'				
I _S	source current	T _{mb} = 25 °C	[1]	-	70	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	242	Α
Avalanche	ruggedness	'				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 61 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; unclamped; Fig. 3		-	48.5	mJ

[1] Continuous current is limited by package

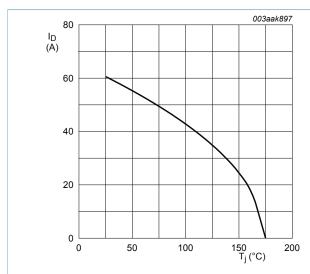


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 V$

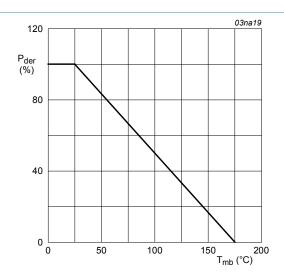


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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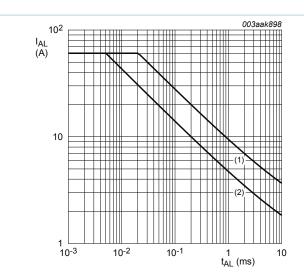
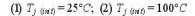


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



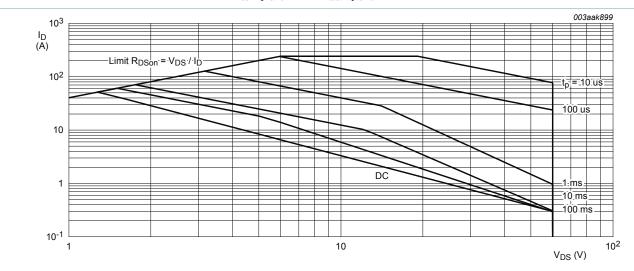


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

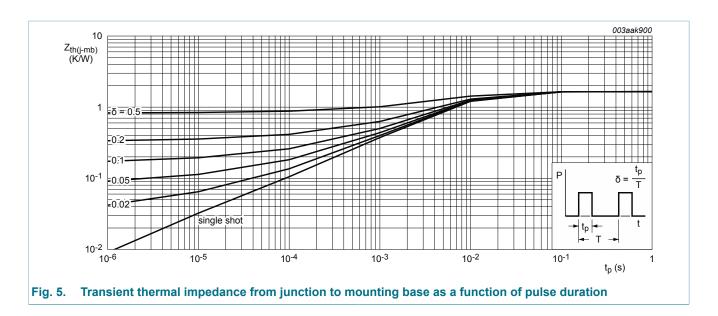
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	1.44	1.65	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 11; Fig. 10	1.3	1.7	2.15	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS} drain leaka	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS} gate leakage curre	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; Fig. 12	-	9.35	11.3	mΩ
		V_{GS} = 4.5 V; I_{D} = 15 A; T_{j} = 25 °C; Fig. 12	-	11	13.1	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	24.8	mΩ
		V _{GS} = 4.5 V; I _D = 15 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	28.8	mΩ
R_G	gate resistance	f = 1 MHz	_	1.86	_	Ω

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 30 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	37.2	-	nC
		I _D = 15 A; V _{DS} = 30 V; V _{GS} = 4.5 V;	-	16.6	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	5	-	nC
Q_{GD}	gate-drain charge		-	5.1	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 15 A; V _{DS} = 30 V; T _j = 25 °C; Fig. 14; Fig. 15	-	2.75	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 16}}$	-	2191	-	pF
C _{oss}	output capacitance	V_{DS} 30 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; <u>Fig. 16</u>	-	199	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$	-	111	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2 \Omega; V_{GS} = 4.5 \text{ V};$	-	13.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	20.2	-	ns
t _{d(off)}	turn-off delay time		-	27.7	-	ns
t _f	fall time		-	15.5	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	20.7	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V; } T_j = 25 \text{ °C}$	-	15.7	-	nC
	I I			1		

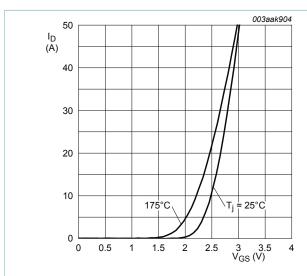


Fig. 6. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = \mathbf{10}V$

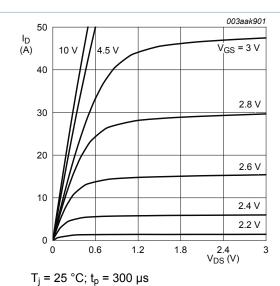


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

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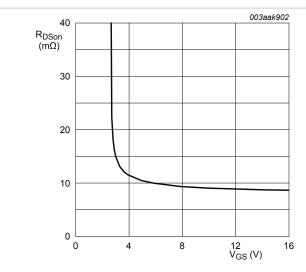


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 15A$

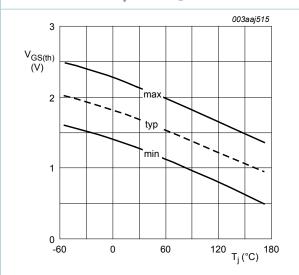


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

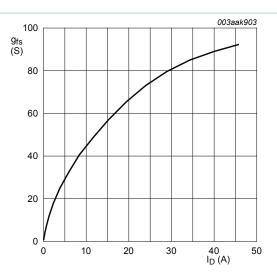


Fig. 9. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; \ V_{DS} = 10V$$

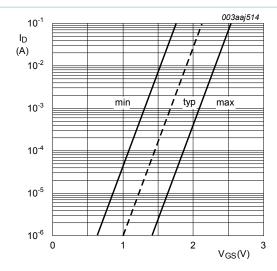


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

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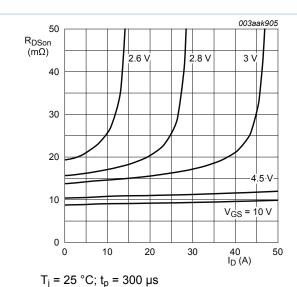


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

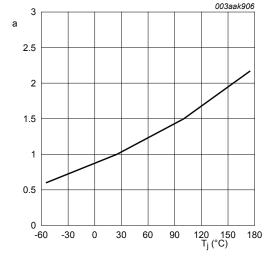


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

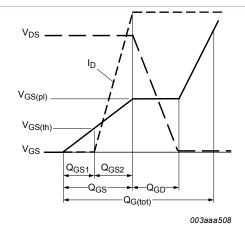


Fig. 14. Gate charge waveform definitions

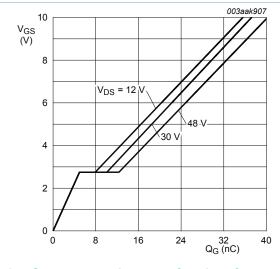


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 15A$

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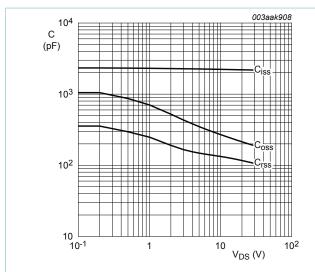
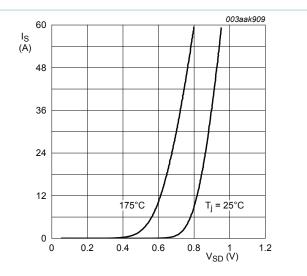


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

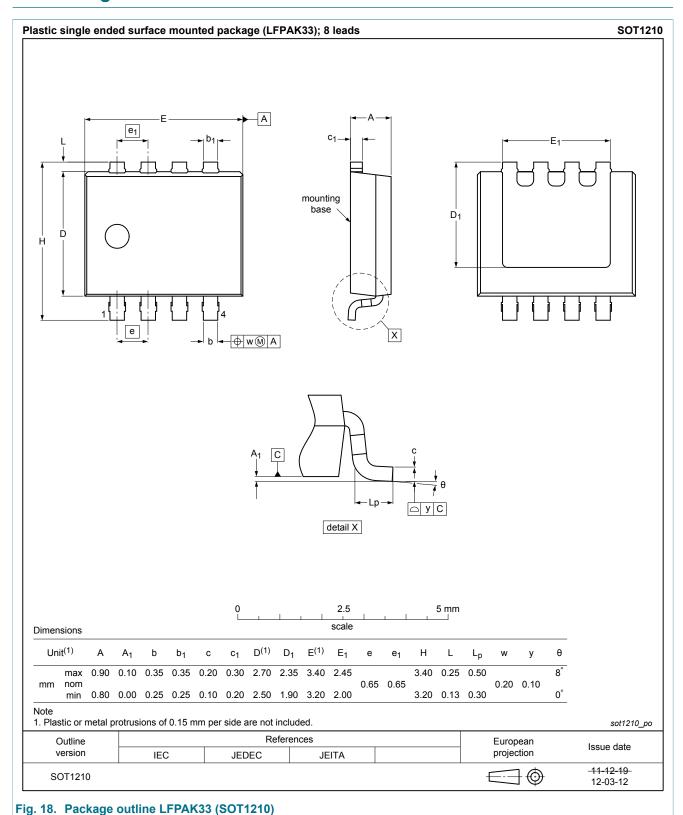
$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$



voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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